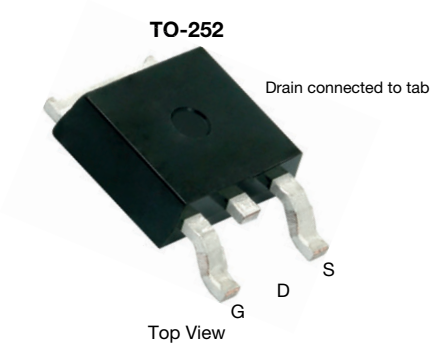
P-Channel 40 V (D-S) 175 °C MOSFET



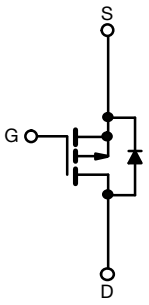
FEATURES

- TrenchFET® Gen IV p-channel power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Motor drive control
- LED backlighting
- Load switch
- Industrial



P-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0120
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.0175
Q_g typ. (nC)	74.3
I_D (A) [d]	-42
Configuration	Single

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and halogen-free	SUD40151EL-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C	I_D	-42 [d]	A
	T_C = 125 °C		-28.6	
Pulsed drain current (t = 100 µs)		I_{DM}	-100	
Continuous source-drain diode current		I_S	-41.7	
Single pulse avalanche current [a]	L = 0.1 mH	I_{AS}	-25	
Single pulse avalanche energy [a]		E_{AS}	31.25	mJ
Maximum power dissipation	T_C = 25 °C	P_D	50 [b]	W
	T_C = 125 °C		16.7 [b]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) [c]		R_{thJA}	60	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	3	

Notes

a. Duty cycle ≤ 1 %
b. See SOA curve for voltage derating
c. When mounted on 1" square PCB (FR4 material)
d. Package limited

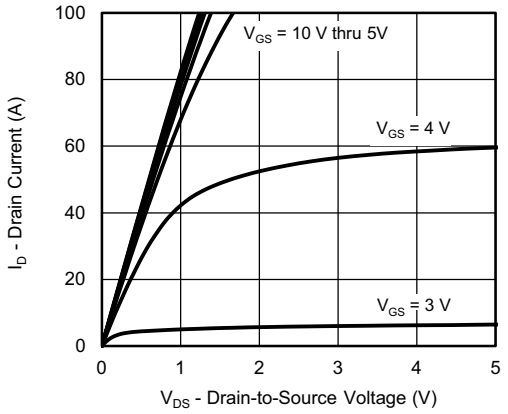
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1.5	-	-2.5	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	250	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -40 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -40 V, V_{GS} = 0 V, T_J = 125 °C	-	-	-150	
		V_{DS} = -40 V, V_{GS} = 0 V, T_J = 175 °C	-	-	-5	mA
On-state drain current [a]	$I_{D(on)}$	V_{DS} ≥ -10 V, V_{GS} = -10 V	-30	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -17.5 A	-	0.0100	0.0120	Ω
		V_{GS} = -4.5 V, I_D = -14.5 A	-	0.0135	0.0175	
Forward transconductance [a]	g_{fs}	V_{DS} = -10 V, I_D = -17.5 A	-	70	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = -20 V, V_{GS} = 0 V, f = 1 MHz	-	5340	-	pF
Output capacitance	C_{oss}		-	335	-	
Reverse transfer capacitance	C_{rss}		-	303	-	
Total gate charge	Q_g	V_{DS} = -20 V, V_{GS} = -10 V, I_D = -17.5 A	-	74.3	112	nC
Gate-source charge	Q_{gs}		-	12.7	-	
Gate-drain charge	Q_{gd}		-	11.1	-	
Gate resistance	R_g	f = 1 MHz	0.86	4.3	8.6	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = -20 V, R_L = 1.4 Ω, I_D ≅ -14 A, V_{GEN} = -10 V, R_g = 1 Ω	-	15	30	ns
Rise time	t_r		-	10	20	
Turn-off delay time	$t_{d(off)}$		-	75	113	
Fall time	t_f		-	75	113	
Drain-Source Body Diode Characteristics						
Pulse diode forward current (t = 100 µs)	I_{SM}		-	-	-42	A
Body diode voltage	V_{SD}	I_F = -14 A, V_{GS} = 0 V	-	-0.85	-1.5	V
Body diode reverse recovery time	t_{rr}	I_F = -14 A, di/dt = 100 A/µs	-	30	45	ns
Body diode reverse recovery charge	Q_{rr}		-	0.02	0.04	µC
Reverse recovery fall time	t_a		-	15.3	-	ns
Reverse recovery rise time	t_b		-	14.7	-	
Body diode peak reverse recovery charge	$I_{RM(REC)}$		-	-	2.8	A

Notes

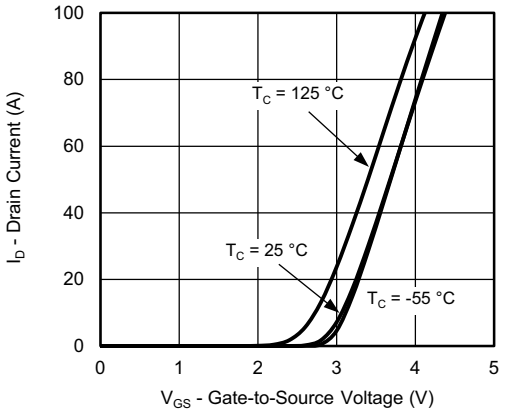
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

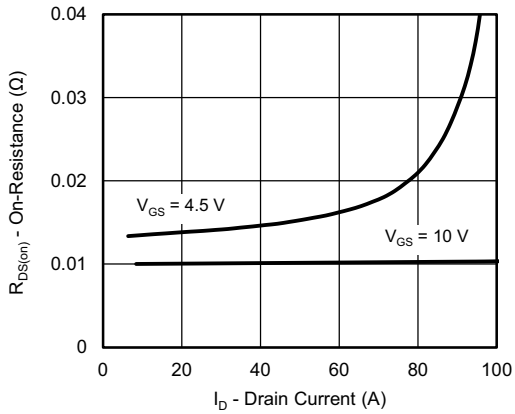
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



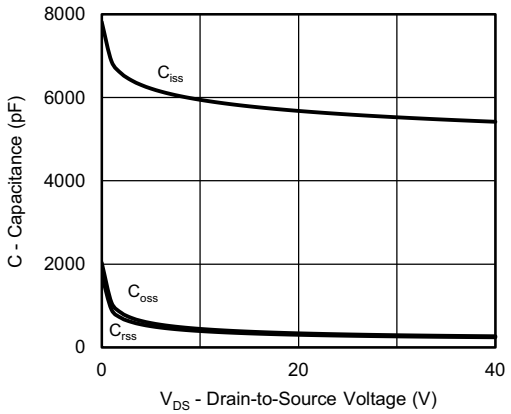
Output Characteristics



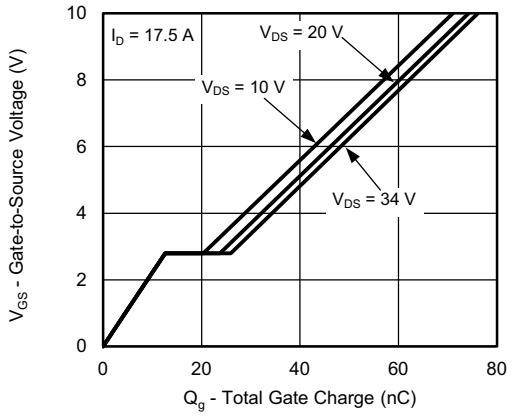
Transfer Characteristics



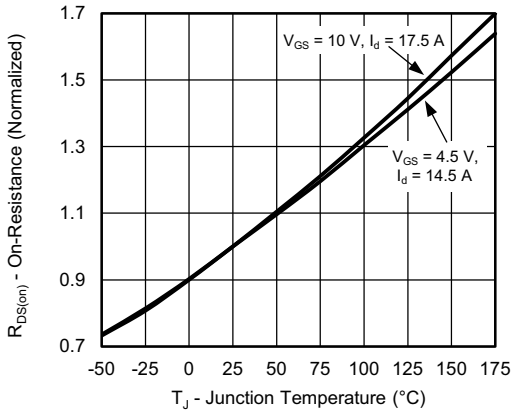
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

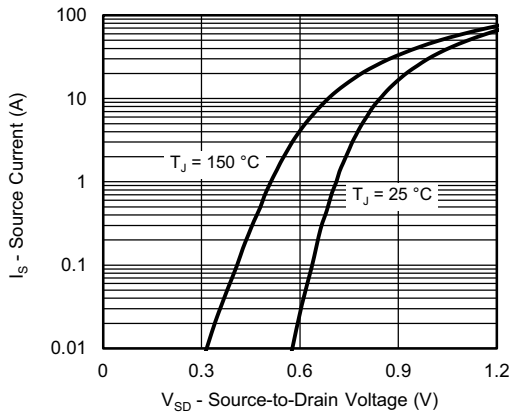


Gate Charge

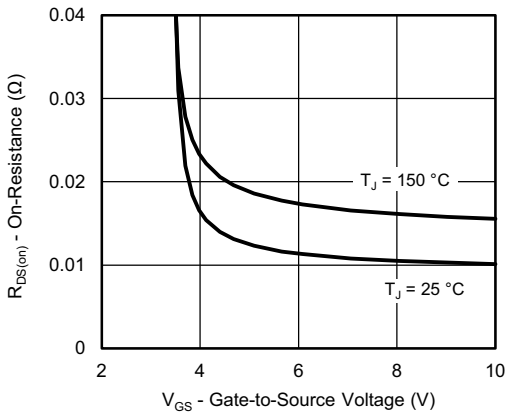


On-Resistance vs. Junction Temperature

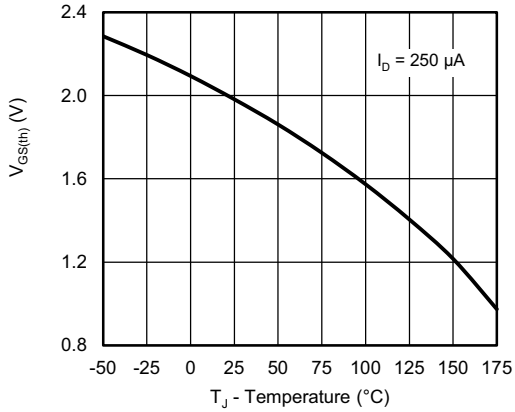
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



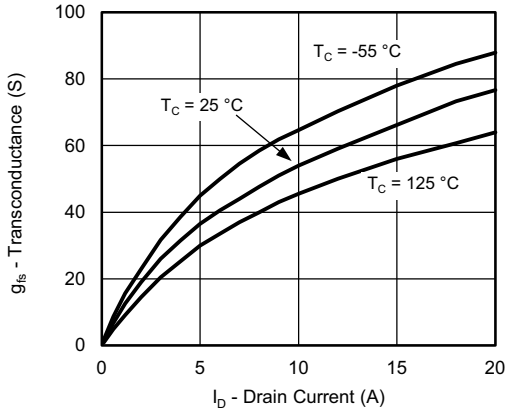
Source-Drain Diode Forward Voltage



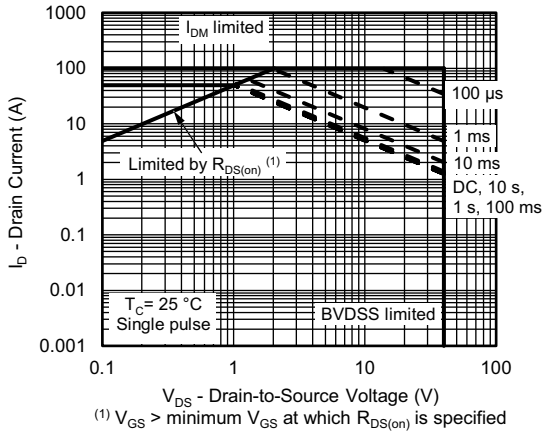
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

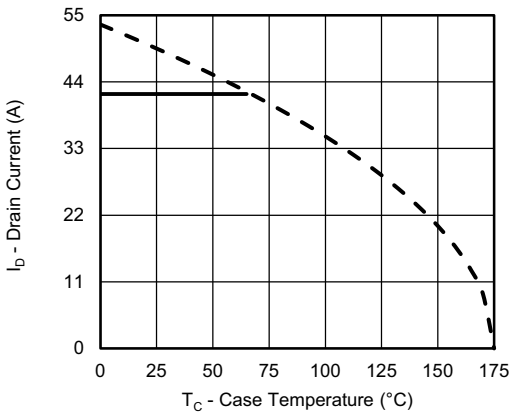


Transconductance

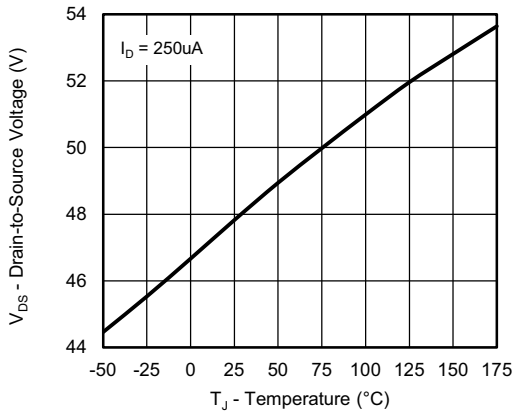


Safe Operating Area, Junction-to-Ambient

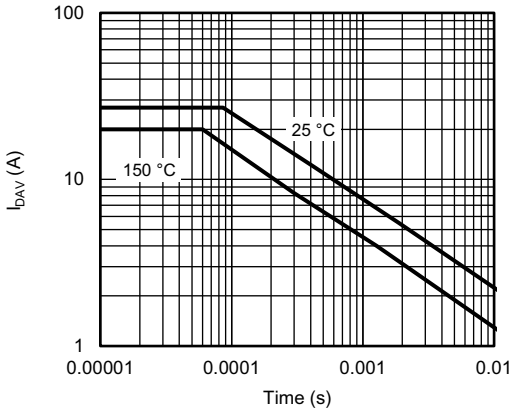
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Drain Source Breakdown vs. Junction Temperature

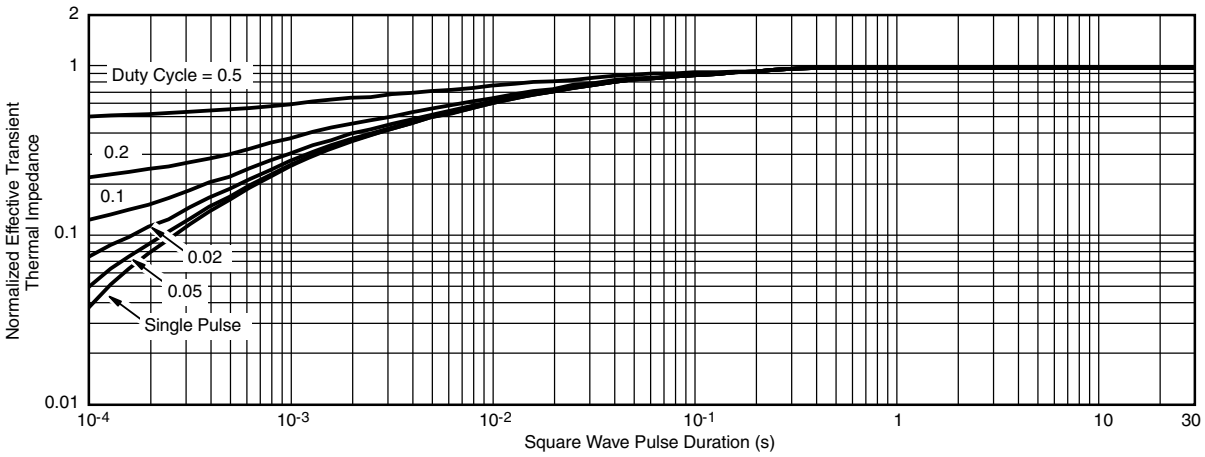


I_{DAV} vs. Time

Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

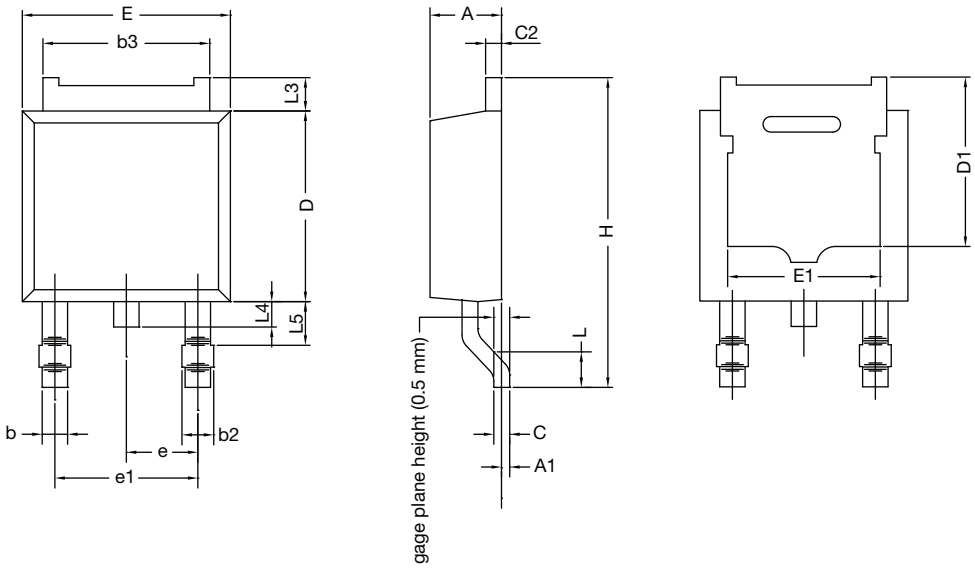


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75668.

TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y

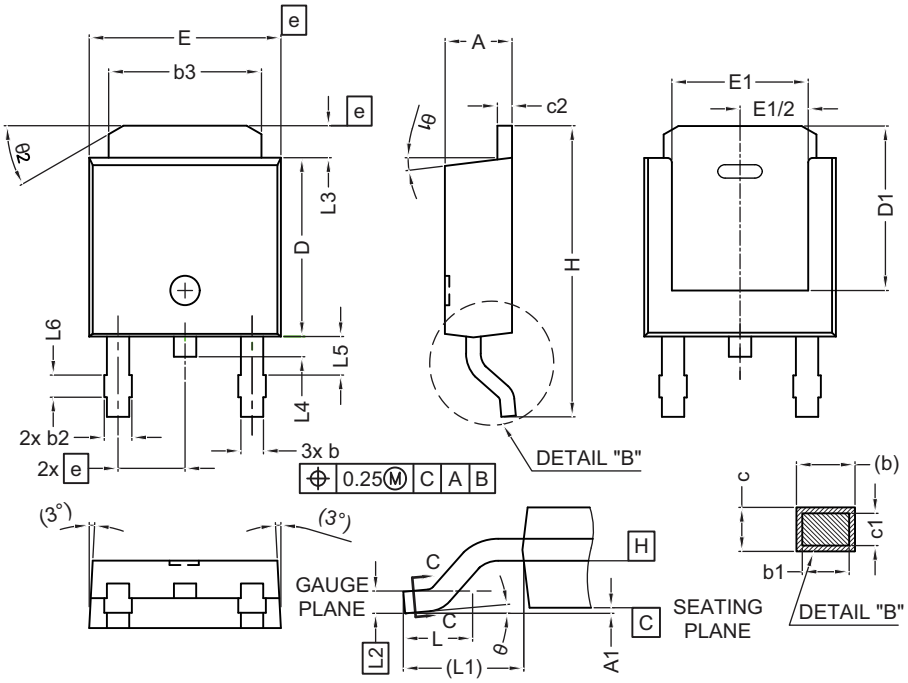


	MILLIMETERS	
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only

VERSION 2: FACILITY CODE = N



	MILLIMETERS	
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

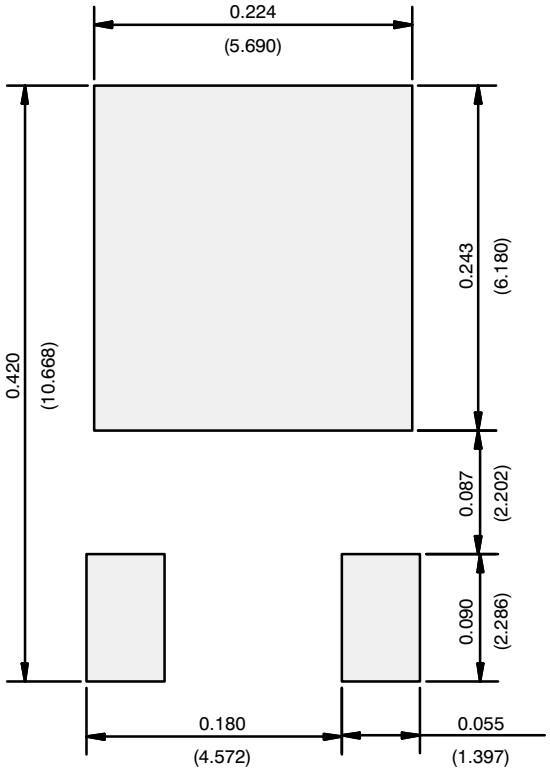
	MILLIMETERS	
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.